



## **Member papers, posters and panel presentations at BACUS 2012**

### Tuesday, September 11

- 9:30 am, Session 3, Patterning – “Improving mask CD uniformity using MB-MDP for 14nm node and beyond,” presented by Samsung Electronics and D2S [8522-04]
- 10:40 am, Session 3, Patterning – “An enhanced measure of mask quality using separated models,” presented by Samsung Electronics and D2S [8522-06]
- 6:00 – 7:30 pm, Poster Session, Mask Data Preparation – “Enhancement of mask process correction (MPC) through dose modulation of already geometrically correct layout data,” presented by SoftJin [8522-77]
- 6:00 – 7:30 pm, Poster Session, Metrology – “Photomask quality evaluation using lithography simulation and precision SEM image contour data,” Advantest and D2S [8522-81]
- 6:00 – 7:30 pm, Poster Session, Mask Pattern Generators – “Proximity effect correction optimizing image quality and writing time for an electron multi-beam mask writer,” presented by Synopsys and IMS Nanofabrication [8522-87]
- 6:00 – 7:30 pm, Poster Session, Mask Pattern Generators – “Evaluation of CP shape correction for e-beam writing,” presented by Advantest and D2S [8522-88]

### Wednesday, September 12

- 2:40 pm, Session 8, Simulation and Modeling – “Advanced module for model parameter extraction using global optimization and sensitivity analysis for electron-beam proximity effect correction,” presented by Aseta Nanographics, Laboratoire des Technologies de la Microelectronique CNRS and Fraunhofer CNT [8522-37]

Thursday, September 13

- 10:40 am, Session 12, Mask Pattern Generators – “Proposal to extend the loading effect correction in EBM-8000,” presented by NuFlare Technology [8522-51]
- 11:00 am, Session 12, Mask Pattern Generators – “Printing results of a proof-of-concept 50keV electron multi-beam mask exposure tool (eMET POC),” presented by IMS Nanofabrication [8522-52]
- 11:20 am, Session 12, Mask Pattern Generators – “Shape-dependent dose margin correction using model-based mask data preparation,” presented by HOYA and D2S [8522-53]
- 11:40 am, Session 12, Mask Pattern Generators – “Reflective electron-beam lithography performance for the 10nm logic node,” presented by KLA-Tencor [8522-54]
- 3:20pm, Special Session Panel Discussion – “Will Optical Patterning Solutions Be Ready if EUV Lithography Continues to Be Delayed?” moderated by Thomas Faure, IBM, and Robert Socha, ASML. Panelists: Allen Gabor, IBM; Aki Fujimura, D2S; Yuri Granik, Mentor Graphics; Yoshio Kawai, ShinEtsu Chemical; Tuan Pham, SanDisk; Geoffery Yeap, Qualcomm; Franklin Kalk, Toppan Photomasks.